PROGRAM

2006 ROCS Workshop

SUNDAY November 12, 2006, Room 213, San Antonio Convention Center
Preceding the Compound Semiconductor IC Symposium. Across from the Marriott Riverwalk Hotel, San Antonio, Texas

SPONSORED BY JEDEC COMMITTEE JC-14.7, EIA, and in cooperation with the IEEE.

Registration  (Cost of Workshop is $200 at the door, make checks payable to JEDEC)  7:30 AM
Welcome, Opening Remarks, Introductions, Start  Anthony Immorlica, Workshop Chairman  8:00 AM

SESSION 1 - Reliability in Emerging Technologies/GaN
Sammy Kayali, Session Chair  8:10 – 10:15 AM

1. Failure Analysis of X-Band GaN FETs. J.L. Jimenez1, Chowdhury1, Balistreri1, Lee1, Saunier1, Chao2, Hu2, Chu2, Immorlica2, del Alamo3, Joh4 and Shur4, 1. TriQuint Semiconductor, Texas, 2. BAE, 3. MIT, 4. RPI


5. Physical Investigation of High-Field Degradation Mechanisms in GaN/AlGaN/GaN HEMTs. M. Faqir1, A. Chin1, Verzellesi1, Fantini1, Rampazzo2, Meneghesso2, Zanoni3, Kordos1, (1) University of Modena, and Reggio Emilia, Italy; (2) University of Padova, Italy, (3) Slovak Academy of Sciences

SESSION 2 - Reliability Topics
Bob Ferro, Session Chair  10:45 AM – Noon


2. Analysis of Lead Free Tin Whisker Test Methodology and Characterization. Helen Cui, Mike Ferrara, RF Micro Devices, Inc. Matthew Mlcak, University of Texas


Lunch  Room 217A  Noon – 1:30 PM

SESSION 3 - HEMT Reliability
Yi-Jen Chan, Session Chair  1:30 – 2:45 PM


SESSION 4 - HBT Reliability
Bill Roesch, Session Chair  3:15 – 4:55 PM


2. Electroluminescence as an instrument to observe defect generation in InGaP/GaAs HBTs. R. Pazirandeh, U. Zeimer, J. Würfl, G. Tränkle , Ferdinand-Braun-Institut für Höchstfrequenztechnik.


4. Defining the safe operating area for HBTs with an InGaP emitter across temperature and current density. Charles S. Whitman, RFMD.

Late Papers  Peter Ersland, Technical Program Chairman  5:00 PM

Website:  http://www.jedec.org/home/gaas/